

LMH6682/6683 190MHz Single Supply, Dual and Triple Operational Amplifiers

General Description

The LMH6682 and LMH6683 are high speed operational amplifiers designed for use in modern video systems. These single supply monolithic amplifiers extend National's feature-rich, high value video portfolio to include a dual and a triple version. The important video specifications of differential gain (± 0.01% typ.) and differential phase (±0.08 degrees) combined with an output drive current in each amplifier of 85mA make the LMH6682 and LMH6683 excellent choices for a full range of video applications.

Voltage feedback topology in operational amplifiers assures maximum flexibility and ease of use in high speed amplifier designs. The LMH6682/83 is fabricated in National Semiconductor's VIP10 process. This advanced process provides a superior ratio of speed to quiescient current consumption and assures the user of high-value amplifier designs. Advanced technology and circuit design enables in these amplifiers a –3db bandwidth of 190MHz, a slew rate of 940V/µsec, and stability for gains of less than –1 and greater than +2.

The input stage design of the LM6682/83 enables an input signal range that extends below the negative rail. The output stage voltage range reaches to within 0.8V of either rail when driving a $2k\Omega$ load. Other attractive features include fast settling and low distortion. Other applications for these amplifiers include servo control designs. These applications are sensitive to amplifiers that exhibit phase reversal when the inputs exceed the rated voltage range. The LMH6682/83 amplifiers are designed to be immune to phase reversal when the specified input range is exceeded. See applications section. This feature makes for design simplicity and flexibility in many industrial applications.

The LMH6682 dual operational amplifier is offered in miniature surface mount packages, SOIC-8, and MSOP-8. The LMH6683 triple amplifier is offered in SOIC-14 and TSSOP-14

Features

 $\rm V_S=\pm 5V,\, T_A=25^{\circ}C,\,\,R_L=100\Omega,\, A=+2$ (Typical values unless specified)

■ DG error 0.01%
 ■ DP error 0.08°
 ■ -3dB BW (A = +2) 190MHz

■ Slew rate (V_S = ±5V) 940V/µs
■ Supply current 6.5mA/amp
■ Output current +80/-90mA

■ Input common mode voltage 0.5V beyond V⁻, 1.7V from

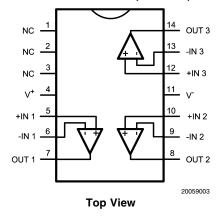
Output voltage swing (R_L = 2kΩ)
 Input voltage noise (100KHz)
 0.8V from rails
 12nV/√Hz

Applications

- CD/DVD ROM
- ADC buffer amp
- Portable video
- Current sense buffer
- Portable communications

Connection Diagrams

SOIC-14/TSSOP-14 (LMH6683)



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DS200590

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

ESD Tolerance

Human Body Model 2KV(Note 2)
Machine Model 200V (Note 3)

V_{IN} Differential ±2.5V Output Short Circuit Duration (Note 4), (Note 6)

Input Current ±10mA

Supply Voltage (V⁺ - V⁻) 12.6V Voltage at Input/Output pins V⁺ +0.8V, V⁻ -0.8V

Soldering Information

Infrared or Convection (20 sec.) 235°C Wave Soldering (10 sec.) 260°C

Storage Temperature Range -65°C to +150°C Junction Temperature (Note 7) +150°C

Operating Ratings (Note 1)

Supply Voltage $(V^+ - V^-)$ 3V to 12V

Operating Temperature Range

(Note 7) -40° C to $+85^{\circ}$ C

Package Thermal Resistance (Note 7)

SOIC-8 190°C/W MSOP-8 235°C/W SOIC-14 145°C/W 155°C/W

TSSOP-14 155°C/W

5V Electrical Characteristics

Unless otherwise specified, all limits guaranteed for at $T_J = 25^{\circ}C$, $V^+ = 5V$, $V^- = 0V$, $V_O = V_{CM} = V^+/2$, and $R_L = 100\Omega$ to $V^+/2$, $R_F = 510\Omega$. **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min	Тур	Max	Units	
			(Note 9)	(Note 8)	(Note 9)		
SSBW	-3dB BW	$A = +2, V_{OUT} = 200 \text{mV}_{PP}$	140	180		MHz	
		$A = -1, V_{OUT} = 200 \text{mV}_{PP}$		180		IVII IZ	
GFP	Gain Flatness Peaking	$A = +2, V_{OUT} = 200 \text{mV}_{PP}$		2.1		dB	
		DC to 100MHz					
GFR	Gain Flatness Rolloff	$A = +2, V_{OUT} = 200 \text{mV}_{PP}$		0.1		dB	
		DC to 100MHz					
LPD 1°	1° Linear Phase Deviation	$A = +2, V_{OUT} = 200 \text{mV}_{PP}, \pm 1^{\circ}$		40		MHz	
GF _{0.1dB}	0.1dB Gain Flatness	$A = +2, \pm 0.1 dB, V_{OUT} = 200 mV_{PP}$		25		MHz	
FPBW	Full Power -1dB Bandwidth	$A = +2$, $V_{OUT} = 2V_{PP}$		110		MHz	
DG	Differential Gain	$A = +2$, $R_L = 150\Omega$ to $V^+/2$		0.03		%	
	NTSC 3.58MHz	Pos video only V _{CM} = 2V					
DP	Differential Phase	$A = +2$, $R_L = 150\Omega$ to $V^+/2$		0.05		deg	
	NTSC 3.58MHz	Pos video only V _{CM} = 2V					
Time Dom	ain Response						
T _r /T _f	Rise and Fall Time	$20-80\%$, $V_O = 1V_{PP}$, $A_V = +2$		2.1		20	
		$20-80\%$, $V_O = 1V_{PP}$, $A_V = -1$		2		ns	
OS	Overshoot	$A = +2, V_O = 100 \text{mV}_{PP}$		22		%	
T _s	Settling Time	$V_O = 2V_{PP}, \pm 0.1\%, A_V = +2$		49		ns	
SR	Slew Rate (Note 11)	$A = +2, V_{OUT} = 3V_{PP}$		520		V/µs	
		$A = -1$, $V_{OUT} = 3V_{PP}$		500		ν/μδ	
Distortion	and Noise Response						
HD2	2 nd Harmonic Distortion	$f = 5MHz, V_O = 2V_{PP}, A = +2, R_L =$		-60			
		2kΩ				dD.a	
		$f = 5MHz$, $V_O = 2V_{PP}$, $A = +2$, $R_L =$		-61		dBc	
		100Ω					
HD3	3 rd Harmonic Distortion	$f = 5MHz, V_O = 2V_{PP}, A = +2, R_L =$		-77			
		2kΩ				dBc	
		$f = 5MHz, V_O = 2V_{PP}, A = +2, R_L =$		-54		ubc	
		100Ω					

5V Electrical Characteristics (Continued) Unless otherwise specified, all limits guaranteed for at $T_J=25^{\circ}C$, $V^+=5V$, $V^-=0V$, $V_O=V_{CM}=V^+/2$, and $R_L=100\Omega$ to $V^+/2$, $R_F=510\Omega$. **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
			(Note 9)	(Note 8)	(Note 9)	
Distortion	and Noise Response					
THD	Total Harmonic Distortion	$f = 5MHz$, $V_O = 2V_{PP}$, $A = +2$, $R_L = 2k\Omega$		-60		dPo
		$f = 5MHz, V_O = 2V_{PP}, A = +2, R_L = 100\Omega$		-53		dBc
e _n	Input Referred Voltage Noise	f = 1kHz		17		nV/ √Hz
		f = 100kHz		12		
i _n	Input Referred Current Noise	f = 1kHz		8		pA/ √Hz
		f = 100kHz		3]
СТ	Cross-Talk Rejection (Amplifier)	f = 5MHz, A = +2, SND: R_L = 100Ω RCV: R_F = R_G = 510Ω		-77		dB
Static, DC	Performance					
A _{VOL}	Large Signal Voltage Gain	$V_{O} = 1.25V \text{ to } 3.75V,$ $R_{L} = 2k\Omega \text{ to } V^{+}/2$	85	95		
		$V_O = 1.5V$ to 3.5V, $R_L = 150\Omega$ to V ⁺ /2	75	85		dB
		$V_O = 2V \text{ to } 3V,$ $R_L = 50\Omega \text{ to } V^+/2$	70	80		
CMVR	Input Common-Mode Voltage Range	CMRR ≥ 50dB	-0.2 -0.1	-0.5		
			3.0 2.8	3.3		· V
V _{OS}	Input Offset Voltage			±1.1	±5 ±7	mV
TC V _{os}	Input Offset Voltage Average Drift	(Note 12)		±2		μV/°C
I _B	Input Bias Current	(Note 10)		-5	-20 -30	μΑ
TC _{IB}	Input Bias Current Drift			0.01		nA/°C
I _{os}	Input Offset Current			50	300 500	nA
CMRR	Common Mode Rejection Ratio	V _{CM} Stepped from 0V to 3.0V	72	82		dB
+PSRR	Positive Power Supply Rejection Ratio	$V^{+} = 4.5V$ to 5.5V, $V_{CM} = 1V$	70	76		dB
I _S	Supply Current (per channel)	No load		6.5	9 11	mA

5V Electrical Characteristics (Continued)

Unless otherwise specified, all limits guaranteed for at $T_J = 25^{\circ}\text{C}$, $V^+ = 5\text{V}$, $V^- = 0\text{V}$, $V_O = V_{CM} = V^+/2$, and $R_L = 100\Omega$ to $V^+/2$, $R_F = 510\Omega$. **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
			(Note 9)	(Note 8)	(Note 9)	
Miscellane	eous Performance		•			
Vo	Output Swing	$R_L = 2k\Omega$ to V ⁺ /2	4.10	4.25		
	High		3.8			
		$R_L = 150\Omega$ to $V^+/2$	3.90	4.19		V
			3.70			V
		$R_L = 75\Omega$ to $V^+/2$	3.75	4.15		
			3.50			
	Output Swing	$R_L = 2k\Omega$ to $V^+/2$		800	920	
	Low				1100	
		$R_L = 150\Omega$ to $V^+/2$		870	970	mV
					1200] ""
		R $_{L}$ = 75 Ω to V ⁺ /2		885	1100	
					1250	
I_{OUT}	Output Current	V _O = 1V from either supply rail	±40	+80/-75		mA
I _{SC}	Output Short Circuit Current	Sourcing to V ⁺ /2	-100	-155		
	(Note 5), (Note 6), (Note 10)		-80			mA
		Sinking from V ⁺ /2	100	220		ША
			80			
R_{IN}	Common Mode Input			3		МΩ
	Resistance					IVIZZ
C _{IN}	Common Mode Input			1.6		pF
	Capacitance					ы
R _{OUT}	Output Resistance Closed	$f = 1kHz, A = +2, R_L = 50\Omega$		0.02		Ω
	Loop	$f = 1MHz, A = +2, R_L = 50\Omega$		0.12		22

±5V Electrical Characteristics

Unless otherwise specified, all limits guaranteed for at $T_J=25^{\circ}C$, $V^+=5V$, $V^-=-5V$, $V_O=V_{CM}=0V$, and $R_L=100\Omega$ to 0V, $R_F=510\Omega$. **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
			(Note 9)	(Note 8)	(Note 9)	
SSBW	-3dB BW	$A = +2, V_{OUT} = 200 \text{mV}_{PP}$	150	190		NAL 1-
		$A = -1$, $V_{OUT} = 200 \text{mV}_{PP}$		190		MHz
GFP	Gain Flatness Peaking	$A = +2, V_{OUT} = 200 \text{mV}_{PP}$ DC to 100MHz		1.7		dB
GFR	Gain Flatness Rolloff	$A = +2, V_{OUT} = 200 \text{mV}_{PP}$ DC to 100MHz		0.1		dB
LPD 1°	1° Linear Phase Deviation	$A = +2, V_{OUT} = 200 \text{mV}_{PP}, \pm 1^{\circ}$		40		MHz
GF _{0.1dB}	0.1dB Gain Flatness	$A = +2, \pm 0.1 dB, V_{OUT} = 200 mV_{PP}$		25		MHz
FPBW	Full Power –1dB Bandwidth	$A = +2$, $V_{OUT} = 2V_{PP}$		120		MHz
DG	Differential Gain NTSC 3.58MHz	$A = +2$, $R_L = 150\Omega$ to 0V		0.01		%
DP	Differential Phase NTSC 3.58MHz	$A = +2$, $R_L = 150\Omega$ to 0V		0.08		deg
Time Dom	ain Response					
T _r /T _f	Rise and Fall Time	20-80%, V _O = 1V _{PP} , A = +2		1.9		
		$20-80\%$, $V_O = 1V_{PP}$, $A = -1$		2		ns
OS	Overshoot	$A = +2, V_O = 100 \text{mV}_{PP}$		19		%
T _s	Settling Time	$V_O = 2V_{PP}, \pm 0.1\%, A = +2$		42		ns

 $\pm 5V$ Electrical Characteristics (Continued) Unless otherwise specified, all limits guaranteed for at $T_J = 25^{\circ}C$, $V^+ = 5V$, $V^- = -5V$, $V_O = V_{CM} = 0V$, and $R_L = 100\Omega$ to 0V, $R_F = 510\Omega$. Boldface limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min (Note 9)	Typ (Note 8)	Max (Note 9)	Units
Time Dom	nain Response	1				
SR	Slew Rate (Note 11)	$A = +2, V_{OUT} = 6V_{PP}$		940		1////
		$A = -1$, $V_{OUT} = 6V_{PP}$		900		V/µs
Distortion	and Noise Response	,				
HD2	2 nd Harmonic Distortion	$f = 5MHz$, $V_O = 2V_{PP}$, $A = +2$, $R_L = 2k\Omega$		-63		
		$f = 5MHz, V_O = 2V_{PP}, A = +2, R_L = 100\Omega$		-66		- dBc
HD3	3 rd Harmonic Distortion	$f = 5MHz$, $V_O = 2V_{PP}$, $A = +2$, $R_L = 2k\Omega$		-82		ID.
		$f = 5MHz, V_O = 2V_{PP}, A = +2, R_L = 100\Omega$		-54		- dBc
THD	Total Harmonic Distortion	$f = 5MHz$, $V_O = 2V_{PP}$, $A = +2$, $R_L = 2k\Omega$		-63		-ID-
		$f = 5MHz, V_O = 2V_{PP}, A = +2, R_L = 100\Omega$		-54		- dBc
e _n	Input Referred Voltage Noise	f = 1kHz		18		nV/ √H:
		f = 100kHz		12		1
i _n	Input Referred Current Noise	f = 1kHz		6		pA/ √H:
		f = 100kHz		3		1
СТ	Cross-Talk Rejection (Amplifier)	f = 5MHz, A = +2, SND: R_L = 100Ω RCV: R_F = R_G = 510Ω		-78		dB
Static, DC	Performance					
A _{VOL}	Large Signal Voltage Gain	$V_{O} = -3.75V$ to 3.75V, $R_{L} = 2k\Omega$ to $V^{+}/2$	87	100		
		$V_{O} = -3.5V \text{ to } 3.5V,$ $R_{L} = 150\Omega \text{ to } V^{+}/2$	80	90		dB
		$V_{O} = -3V \text{ to } 3V,$ $R_{L} = 50\Omega \text{ to } V^{+}/2$	75	85		
CMVR	Input Common Mode Voltage Range	CMRR ≥ 50dB	-5.2 -5.1	-5.5		V
			3.0 2.8	3.3		
V _{OS}	Input Offset Voltage			±1	±5 ±7	mV
TC V _{OS}	Input Offset Voltage Average Drift	(Note 12)		±2		μV/°C
I _B	Input Bias Current	(Note 10)		-5	-20 -30	μА
TC _{IB}	Input Bias Current Drift			0.01		nA/°C
I _{os}	Input Offset Current			50	300 500	nA
CMRR	Common Mode Rejection Ratio	V _{CM} Stepped from –5V to 3.0V	75	84		dB
+PSRR	Positive Power Supply Rejection Ratio	$V^{+} = 8.5V \text{ to } 9.5V,$ $V^{-} = -1V$	75	82		dB
-PSRR	Negative Power Supply Rejection Ratio	$V^{-} = -4.5V \text{ to } -5.5V,$ $V^{+} = 5V$	78	85		dB

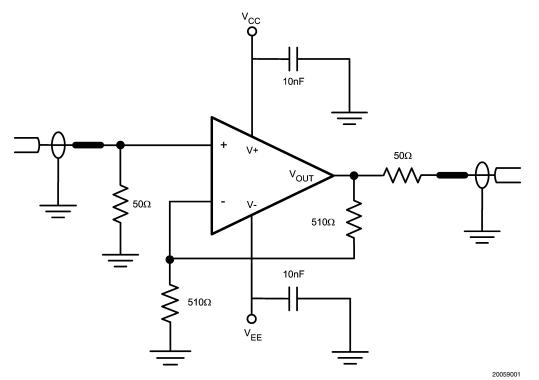
±5V Electrical Characteristics (Continued)

Unless otherwise specified, all limits guaranteed for at $T_J = 25^{\circ}C$, $V^+ = 5V$, $V^- = -5V$, $V_O = V_{CM} = 0V$, and $R_L = 100\Omega$ to 0V, $R_F = 510\Omega$. **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min (Note 9)	Typ (Note 8)	Max (Note 9)	Units
Static, DC	Performance		'	'		
Is	Supply Current (per channel)	No load		6.5	9.5 11	mA
Miscellane	ous Performance	•	•			
V _O	Output Swing High	$R_L = 2k\Omega$ to 0V	4.10 3.80	4.25		
		$R_L = 150\Omega$ to 0V	3.90 3.70	4.20		V
		$R_L = 75\Omega$ to 0V	3.75 3.50	4.18		
	Output Swing Low	$R_L = 2k\Omega$ to 0V		-4.19	-4.07 - 3.80	
		$R_L = 150\Omega$ to 0V		-4.05	-3.89 -3.65	mV
		R $_{L} = 75\Omega$ to 0V		-4.00	-3.70 -3.50	
I _{OUT}	Output Current	V _O = 1V from either supply rail	±45	+85/-80		mA
I _{sc}	Output Short Circuit Current (Note 5), (Note 6),(Note 10)	Sourcing to 0V	-120 -100	-180		mA
		Sinking from 0V	120 100	230		ША
R _{IN}	Common Mode Input Resistance			4		МΩ
C _{IN}	Common Mode Input Capacitance			1.6		pF
R _{OUT}	Output Resistance Closed Loop	$f = 1 \text{kHz}, A = +2, R_L = 50Ω$ $f = 1 \text{MHz}, A = +2, R_L = 50Ω$		0.02 0.12		Ω

- Note 1: Absolute maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not guaranteed. For guaranteed specifications and the test conditions, see the Electrical Characteristics.
- Note 2: Human body model, $1.5k\Omega$ in series with 100pF.
- Note 3: Machine Model, 0Ω in series with 200pF.
- Note 4: Applies to both single-supply and split-supply operation. Continuous short circuit operation at elevated ambient temperature can result in exceeding the maximum allowed junction temperature of 150°C.
- Note 5: Short circuit test is a momentary test. See next note.
- Note 6: Output short circuit duration is infinite for $V_S < 6V$ at room temperature and below. For $V_S > 6V$, allowable short circuit duration is 1.5ms.
- Note 7: The maximum power dissipation is a function of $T_{J(MAX)}$, θ_{JA} , and T_A . The maximum allowable power dissipation at any ambient temperature is $P_D = (T_{J(MAX)} T_A) / \theta_{JA}$. All numbers apply for packages soldered directly onto a PC board.
- Note 8: Typical values represent the most likely parametric norm.
- Note 9: All limits are guaranteed by testing or statistical analysis.
- Note 10: Positive current corresponds to current flowing into the device.
- Note 11: Slew rate is the average of the rising and falling slew rates
- Note 12: Offset Voltage average drift determined by dividing the change in VOS at temperature extremes into the total temperature change.

Typical Schematic



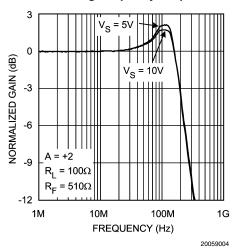
Ordering Information

Package	Part Number	Package Marking	Transport Media	NSC Drawing	
8-Pin SOIC	LMH6682MA	LMH6682MA	95 Units/Rail	M08A	
	LMH6682MAX	LIVINOOZIVIA	2.5k Units Tape and Reel	IVIUOA	
8-Pin MSOP	LMH6682MM	A90A	1k Units Tape and Reel	MUA08A	
	LMH6682MMX		2.5k Units Tape and Reel	IVIOAUOA	
14-Pin SOIC	LMH6683MA	LMH6683MA	55 Units/Rail	M14A	
	LMH6683MAX	LIVINDOOSIVIA	2.5k Units Tape and Reel	IVI 14A	
14-Pin	LMH6683MT	LMUGGOOMT	94 Units/Rail	MTC14	
TSSOP	LMH6683MTX	LMH6683MTX LMH6683MT 2.5 Units Tape		WITC14	

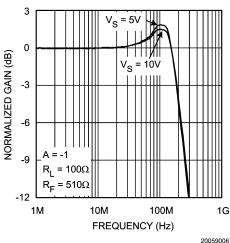
Typical Performance Characteristics

At $T_A = 25^{\circ}C$, $V^+ = +5V$, $V^- = -5V$, $R_F = 510\Omega$ for A = +2; unless otherwise specified.

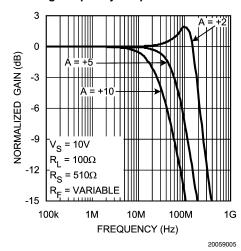
Non-Inverting Frequency Response



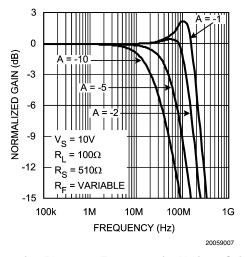
Inverting Frequency Response



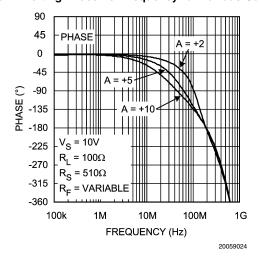
Non-Inverting Frequency Response for Various Gain



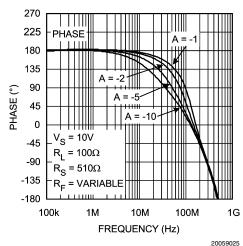
Inverting Frequency Response for Various Gain



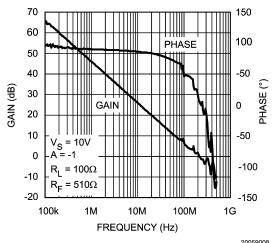
Non-Inverting Phase vs. Frequency for Various Gain



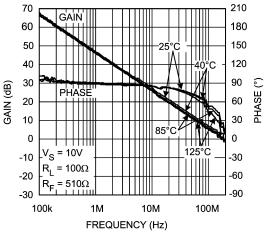
Inverting Phase vs. Frequency for Various Gain



Open Loop Gain & Phase vs. Frequency

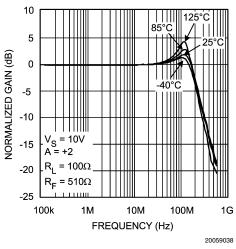


Open Loop Gain and Phase vs. Frequency Over Temperature

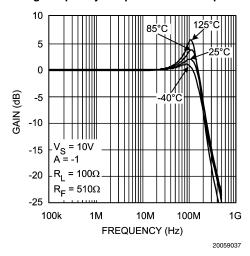


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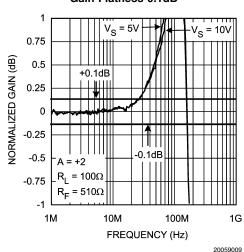
Non-Inverting Frequency Response Over Temperature



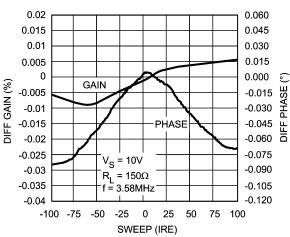
Inverting Frequency Response Over Temperature



Gain Flatness 0.1dB

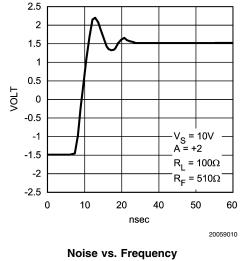


Differential Gain & Phase for A = +2

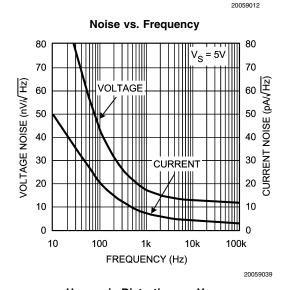


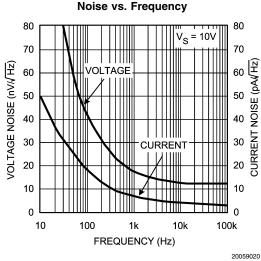
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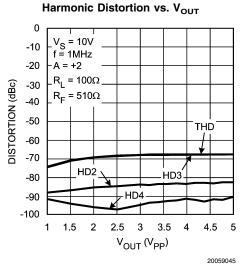
Transient Response Negative 2.5 V_S = 10V A = +2 2 1.5 $R_L = 100\Omega$ $R_F = 510\Omega$ 1 0.5 VOLT 0 -0.5 -1.5 -2 -2.5 0 10 20 30 40 50 nsec

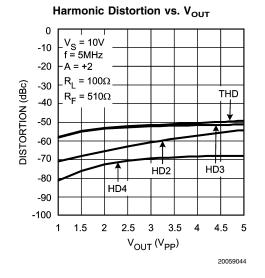


Transient Response Positive

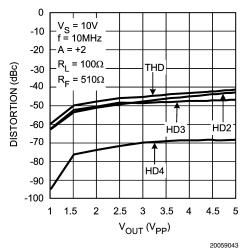




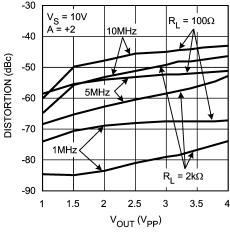




Harmonic Distortion vs. V_{OUT}

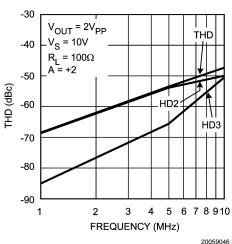


THD vs. for Various Frequencies

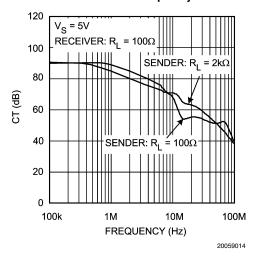


2005904

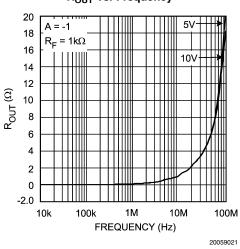
Harmonic Distortion vs. Frequency



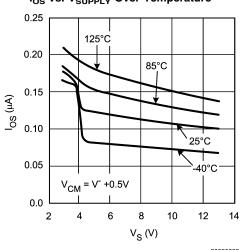
Crosstalk vs. Frequency



R_{OUT} vs. Frequency



 I_{OS} vs. V_{SUPPLY} Over Temperature

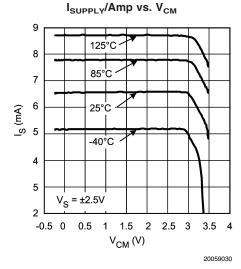


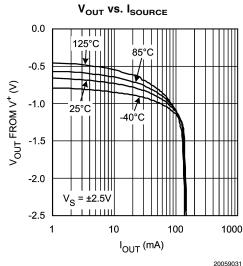
20059023

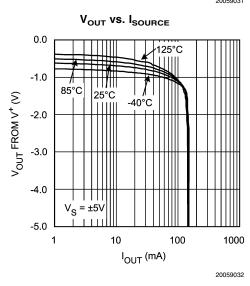
Typical Performance Characteristics (Continued) $V_{\rm OS}$ vs. $V_{\rm S}$ @ -40°C V_{OS} vs. V_{S} @ 25°C 0.0 0.0 UNIT 3 UNIT 1 UNIT 3 UNIT 1 -0.5 -0.5 -1.0 -1.0 -1.5 -1.5 V_{OS} (mV) V_{OS} (mV) -2.0 -2.0 UNIT 4 UNIT 2 -2.5 -2.5 UNIT 4 -3.0 -3.0 UNIT 2 -3.5 -3.5 -4.0 -4.0 $V_{CM} = V^- + 0.5V$ T = -40°C V_{CM} = V⁻ +0.5V -T = 25°C -4.5 -4.5 -5.0 -5.0 2 6 10 6 8 12 14 8 10 12 14 $V_{S}(V)$ $V_{S}(V)$ 20059047 20059048 V_{OS} vs. V_{S} @ 85°C V_{os} vs. V_s @ 125°C 0.0 0.0 UNIT 1 UNIT 1 -0.5 -0.5 UNIT 3 UNIT 3 -1.0 -1.0 -1.5 -1.5 -2.0 V_{OS} (mV) -2.0 V_{OS} (mV) UNIT 2 -2.5 -2.5 UNIT 4 -3.0 -3.0 -3.5 -3.5 -4.0 -4.0 $V_{CM} = V^{-} + 0.5V$ $V_{CM} = V^{-} + 0.5V$ -4.5 -4.5 T = 85°C ″125°C UNIT 2 UNIT 4 -5.0 -5.0 8 6 8 2 6 10 12 14 2 10 12 14 $V_{S}(V)$ $V_{S}(V)$ 20059049 20059050 ${ m V}_{ m OS}$ vs. ${ m V}_{ m OUT}$ V_{OS} vs. V_{OUT} 5.0 5.0 $V_S = \pm 2.5 V$ -125°C $V_S = \pm 5V$ 125°C $R_L = 150\Omega$ $R_L = 150\Omega$ -85°C 3.0 3.0 85°C 1 1 -25°C 25°C 1.0 1.0 V_{OS} (mV) V_{OS} (mV) -40°C -40°C -1.0 -1.0 -40°C -40°C 25°C 25°C -3.0 -3.0 85°C-85°C 125°C 125°C -5.0 -5.0 -2 -1.5 -1 0 0.5 -5 -4 -3 -2 -1 0 -0.5 1 2 1.5 $V_{OUT}(V)$ $V_{OUT}(V)$

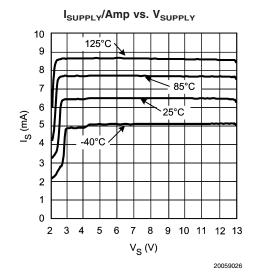
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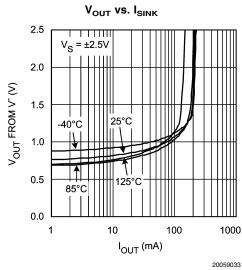
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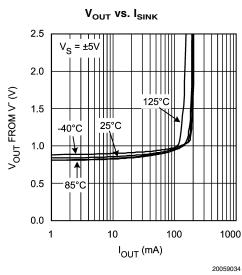


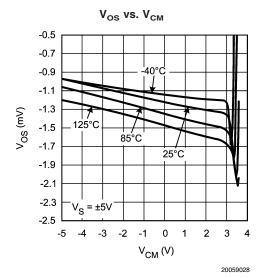


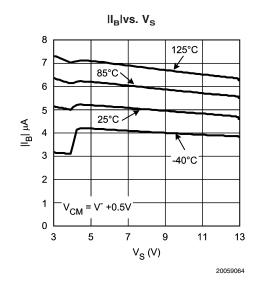


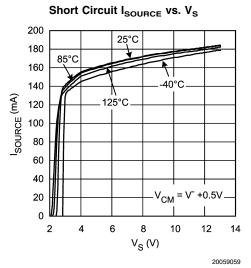


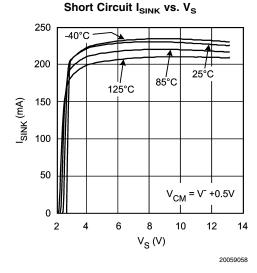


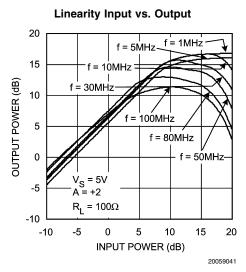


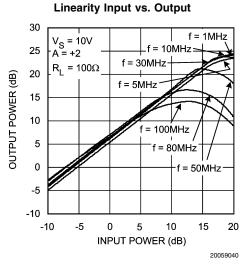












$\begin{array}{c} 120 \\ 100 \\ 80 \\ R_{F} = 510\Omega \\ 20 \\ R_{L} = 100\Omega \\ \end{array}$

CMRR vs. Frequency

Small Signal Pulse Response for A = +2

100k

1M

FREQUENCY (Hz)

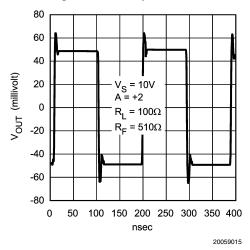
10M

100M

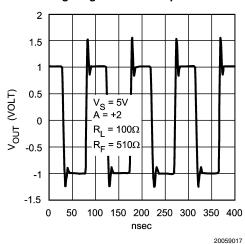
20059022

10k

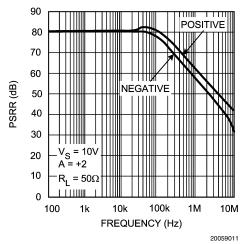
1k

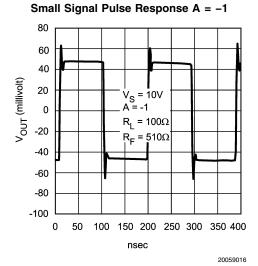


Large Signal Pulse Response

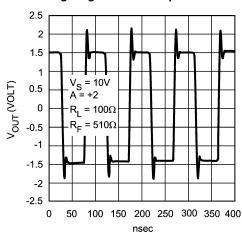


PSRR vs. Frequency





Large Signal Pulse Response



20059018

Applications Section

LARGE SIGNAL BEHAVIOR

Amplifying high frequency signals with large amplitudes (as in video applications) has some special aspects to look after. The bandwidth of the Op Amp for large amplitudes is less than the small signal bandwidth because of slew rate limitations. While amplifying pulse shaped signals the slew rate properties of the OpAmp become more important at higher amplitude ranges. Due to the internal structure of an Op Amp the output can only change with a limited voltage difference per time unit (dV/dt). This can be explained as follows: To keep it simple, assume that an Op Amp consists of two parts; the input stage and the output stage. In order to stabilize the Op Amp, the output stage has a compensation capacitor in its feedback path. This Miller C integrates the current from the input stage and determines the pulse response of the Op Amp. The input stage must charge/discharge the feedback capacitor, as can be seen in Figure 1.

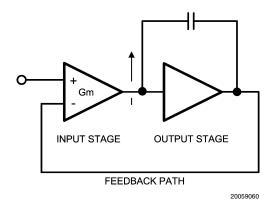


FIGURE 1.

When a voltage transient is applied to the non inverting input of the Op Amp, the current from the input stage will charge the capacitor and the output voltage will slope up. The overall feedback will subtract the gradually increasing output voltage from the input voltage. The decreasing differential input voltage is converted into a current by the input stage (Gm).

$$I^* \Delta t = C ^* \Delta V$$
 (1)

$$\Delta V/\Delta t = I/C \tag{2}$$

$$I=\Delta V^*Gm$$
 (3)

where I = current

t = time

C = capacitance

V = voltage

Gm = transconductance

Slew rate $\Delta V/\Delta t = \text{volt/second}$

In most amplifier designs the current I is limited for high differential voltages (Gm becomes zero). The slew rate will than be limited as well:

$$\Delta V/\Delta t = Imax/C \tag{4}$$

16

The LMH6682/83 has a different setup of the input stage. It has the property to deliver more current to the output stage when the input voltage is higher (class AB input). The current into the Miller capacitor exhibits an exponential character, while this current in other Op Amp designs reaches a saturation level at high input levels: (see *Figure 2*)

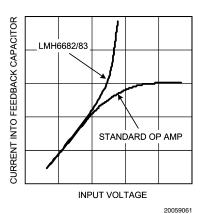
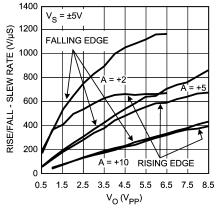


FIGURE 2.

This property of the LMH6682/83 guaranties a higher slew rate at higher differential input voltages.

$$\Delta V/\Delta t = \Delta V^* Gm/C \tag{5}$$

In Figure 3 one can see that a higher transient voltage than will lead to a higher slew rate.



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FIGURE 3.

HANDLING VIDEO SIGNALS

When handling video signals, two aspects are very important especially when cascading amplifiers in a NTSC- or PAL video system. A composite video signal consists of both amplitude and phase information. The amplitude represents saturation while phase determines color (color burst is 3.59MHz for NTSC and 4.58MHz for PAL systems). In this case it is not only important to have an accurate amplification of the amplitude but also it is important not to add a varying phase shift to the video signals. It is a known phenomena that at different dc levels over a certain load the phase of the amplified signal will vary a little bit. In a video chain many amplifiers will be cascaded and all errors will be added together. For this reason, it is necessary to have strict requirements for the variation in gain and phase in conjunction to different dc levels. As can be seen in the tables the number for the differential gain for the LMH6682/83 is only 0.01% and for the differential phase it is only 0.08° at a supply voltage of ±5V. Note that the phase is very depen-

Applications Section (Continued)

dent of the load resistance, mainly because of the dc current delivered by the parts output stage into the load. For more information about differential gain and phase and how to measure it see National Semiconductors application note OA-24 which can be found on via Nationals home page http://www.national.com

OUTPUT PHASE REVERSAL

This is a problem with some operational amplifiers. This effect is caused by phase reversal in the input stage due to saturation of one or more of the transistors when the inputs exceed the normal expected range of voltages. Some applications, such as servo control loops among others, are sensitive to this kind of behavior and would need special safeguards to ensure proper functioning. The LMH6682/6683 is immune to output phase reversal with input overload. With inputs exceeded, the LMH6682/6683 output will stay at the clamped voltage from the supply rail. Exceeding the input supply voltages beyond the Absolute Maximum Ratings of the device could however damage or otherwise adversely effect the reliability or life of the device.

DRIVING CAPACITIVE LOADS

The LMH6682/6683 can drive moderate values of capacitance by utilizing a series isolation resistor between the output and the capacitive load. Capacitive load tolerance will improve with higher closed loop gain values. Applications such as ADC buffers, among others, present complex and varying capacitive loads to the Op Amp; best value for this isolation resistance is often found by experimentation and actual trial and error for each application.

DISTORTION

Applications with demanding distortion performance requirements are best served with the device operating in the inverting mode. The reason for this is that in the inverting configuration, the input common mode voltage does not vary with the signal and there is no subsequent ill effects due to this shift in operating point and the possibility of additional non-linearity. Moreover, under low closed loop gain settings (most suited to low distortion), the non-inverting configuration is at a further disadvantage of having to contend with the input common voltage range. There is also a strong relationship between output loading and distortion performance (i.e. $2k\Omega$ vs. 100Ω distortion improves by about 15dB @1MHz) especially at the lower frequency end where the distortion tends to be lower. At higher frequency, this dependence diminishes greatly such that this difference is only about 5dB at 10MHz. But, in general, lighter output load leads to reduced HD3 term and thus improves THD. (see the curve THD vs. V_{OUT} over various frequencies).

PRINTED CIRCUIT BOARD LAYOUT AND COMPONENT VALUES SELECTION

Generally it is a good idea to keep in mind that for a good high frequency design both the active parts and the passive ones are suitable for the purpose you are using them for. Amplifying frequencies of several hundreds of MHz is possible while using standard resistors but it makes life much easier when using surface mount ones. These resistors (and capacitors) are smaller and therefore parasitics have lower values and will have less influence on the properties of the amplifier. Another important issue is the PCB, which is no longer a simple carrier for all the parts and a medium to

interconnect them. The board becomes a real part itself, adding its own high frequency properties to the overall performance of the circuit. It's good practice to have at least one ground plane on a PCB giving a low impedance path for all decouplings and other ground connections. Care should be taken especially that on board transmission lines have the same impedance as the cables they are connected to (i.e. 50Ω for most applications and 75Ω in case of video and cable TV applications). These transmission lines usually require much wider traces on a standard double sided PCB than needed for a 'normal' connection. Another important issue is that inputs and outputs must not 'see' each other or are routed together over the PCB at a small distance. Furthermore it is important that components are placed as flat as possible on the surface of the PCB. For higher frequencies a long lead can act as a coil, a capacitor or an antenna. A pair of leads can even form a transformer. Careful design of the PCB avoids oscillations or other unwanted behavior. When working with really high frequencies, the only components which can be used will be the surface mount ones (for more information see OA-15).

As an example of how important the component values are for the behavior of your circuit, look at the following case: On a board with good high frequency layout, an amplifier is placed. For the two (equal) resistors in the feedback path, 5 different values are used to set the gain to +2. The resistors vary from 200Ω to $3k\Omega$.

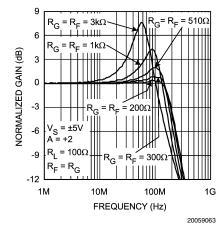


FIGURE 4.

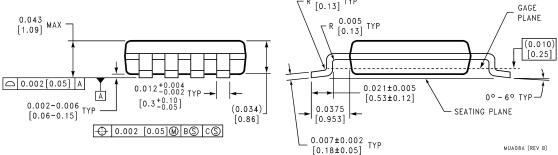
In *Figure 4* can be seen that there's more peaking with higher resistor values, which can lead to oscillations and bad pulse responses. On the other hand the low resistor values will contribute to higher overall power consumption.

NSC suggests the following evaluation boards as a guide for high frequency layout and as an aid in device testing and characterization.

Device	Package	Evaluation
		Board PN
LMH6682MA	8-Pin SOIC	CLC730036
LMH6682MM	8-Pin MSOP	CLC730123
LMH6683MA	14-Pin SOIC	CLC730031
LMH6683MT	14-Pin TSSOP	CLC730131

These free evaluation boards are shipped when a device sample request is placed with National Semiconductor.

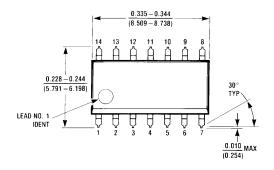
Physical Dimensions inches (millimeters) unless otherwise noted 0.228 - 0.244 (5.791 - 6.198) 0.010 MAX $\sqrt{(0.254)}$ LEAD NO. 1 IDENT $\frac{0.150 - 0.157}{(3.810 - 3.988)}$ $\frac{0.053 - 0.069}{(1.346 - 1.753)}$ $0.010 - 0.020 \times 45$ (0.254 - 0.508)8° MAX TYP ALL LEADS 0.004 - 0.010(0.102 - 0.254)SEATING 0.004 0.050 (1.270) TYP 0.008 - 0.0100.014 - 0.020 (0.356 - 0.508) ALL LEAD TIPS 0.016 - 0.050 (0.356)(0.203 – 0.254) TYP ALL LEADS (0.406 - 1.270) TYP ALL LEADS 0.008 (0.203) TYP 8-Pin SOIC **NS Package Number M08A** 0.118±0.004 B [3±0.1] С (0.189)0.118±0.004 0.193±0.004 [4.8] $[3 \pm 0.1]$ [4.9±0.1] (0.040)TYP [1.02] PIN 1 IDENT NOTE 2 (0.016)(0.0256) _{TYP} [0.41] [0.65] LAND PATTERN RECOMMENDATION (0.0256) TYP [0.65] 0.005 [0.13] TYP GAGE 0.043 [1.09] MAX PLANE R [0.005 TYP (0.010) [0.25]

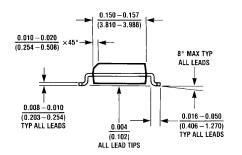


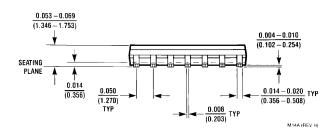
8-Pin MSOP
NS Package Number MUA08A

18

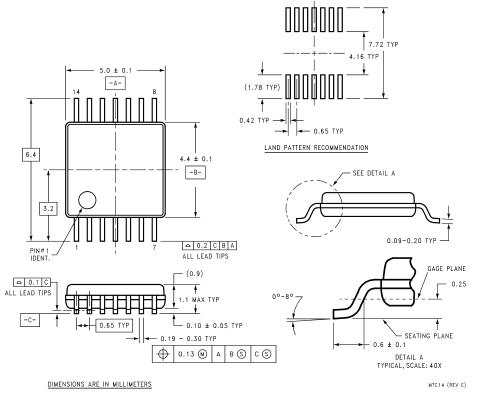
Physical Dimensions inches (millimeters) unless otherwise noted (Continued)







14-Pin SOIC NS Package Number M14A



14-Pin TSSOP NS Package Number MTC14

Notes

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